

01/14/02
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PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

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|---|--|--|--|----------|--|----------------------------------|--|----------|--|
| APPLICATION: | | CLASS | | SUBCLASS | | GAU | | EXAMINER | |
| APPL NUM | | FILING DATE | | CLASS | | SUBCLASS | | GAU | |
| 10047323 | | 01/14/2002 | | 427 | | 104 | | 1762 | |
| **APPLICANTS: Lampert William; Eiting Christopher; Smith Scott; Haas Trice; | | | | | | | | | |
| **CONTINUING DATA VERIFIED: THIS APPLN CLAIMS BENEFIT OF 60/265,167 01/30/2001 | | | | | | | | | |
| ** FOREIGN APPLICATIONS VERIFIED: | | | | | | | | | |
| PG-PUB | | DO NOT PUBLISH <input checked="" type="checkbox"/> | | | | RESCIND <input type="checkbox"/> | | | |
| Foreign priority claimed | | <input type="checkbox"/> yes <input type="checkbox"/> no | | | | ATTORNEY DOCKET NO | | | |
| 35 USC 119 conditions met | | <input type="checkbox"/> yes <input type="checkbox"/> no | | | | AFD 504 | | | |
| Verified and Acknowledged Examiners's initials | | | | | | | | | |
| TITLE : Method of growing homoepitaxial silicon carbide | | | | | | | | | |

U.S. DEPT. OF COMM. PAT & TM-PTO-436L (Rev. 12-94)

| | | | |
|----------------------------|--|---|---------------------|
| NOTICE OF ALLOWANCE MAILED | | CLAIMS ALLOWED | |
| | | Total Claims | Print Claim for 0.6 |
| Assistant Examiner | | DRAWING | |
| Amount Due | | Sheets Drawg. | Figs. Drawg. |
| Date Paid | | Print Fig. | |
| Primary Examiner | | Application Examiner | |
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